Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | 30 | V |
| V _{GS} | gate-source voltage | | | -20 | - | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | - | 3.7 | Α |
| Static characte | Static characteristics | | | | | | , |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$ | | - | 54 | 72 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|-------------------------|----------------|
| 1 | G | gate | 3 | D I |
| 2 | S | source | | |
| 3 | D | drain | 1 2 TO-236AB (SOT23) | G S 017aaa255 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|----------|--|---------|--|--|
| | Name | Description | Version | | |
| PMV90ENE | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code [1] |
|-------------|------------------|
| PMV90ENE | %GH |

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 30 | V |
| V_{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 3.7 | Α |
| | | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | 3 | Α |
| | | V _{GS} = 10 V; T _{amb} = 100 °C | [1] | - | 1.9 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs | | - | 12 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 460 | mW |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|----------------------|--------------------------|-----|-----|-----|------|
| | | | [1] | - | 1.1 | W |
| | | T _{sp} = 25 °C | | - | 4.5 | W |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-dra | in diode | 1 | , | | | |
| Is | source current | T _{amb} = 25 °C | [1] | - | 1 | Α |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

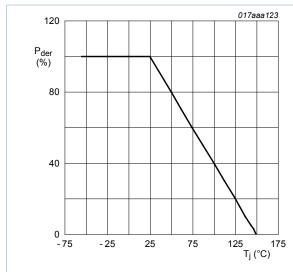


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

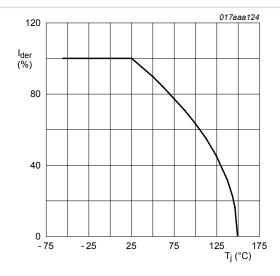


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

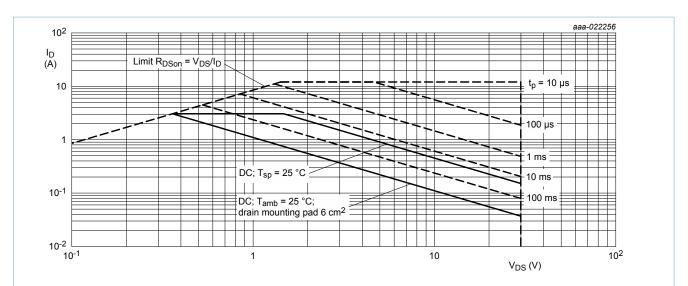


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

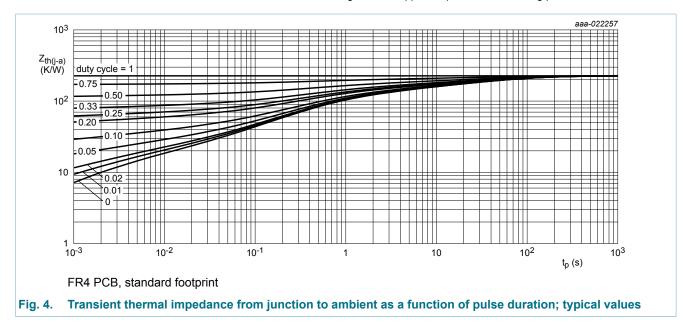
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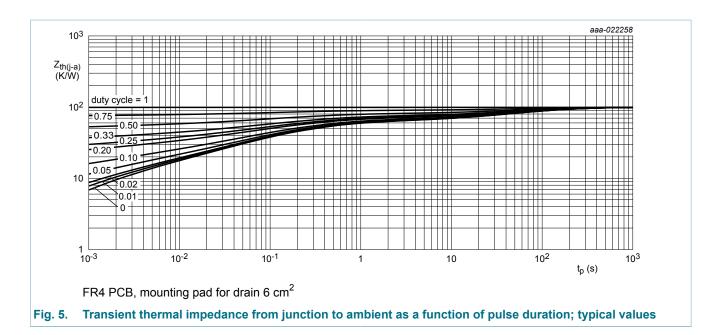
9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--|--|-------------|-----|-----|-----|-----|------|
| R _{th(j-a)} thermal resistance from junction to ambient | | in free air | [1] | - | 227 | 270 | K/W |
| | | [2] | - | 99 | 115 | K/W | |
| | ambient | t ≤ 5 s | [2] | - | 66 | 78 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 20 | 28 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².





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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--|---|--|-----|------|-----|------|
| Static char | acteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 30 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \degree C$ | 1 | 1.5 | 2.5 | V |
| I _{DSS} | drain leakage current | V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μA |
| I _{GSS} gate le | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μA |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -10 | μΑ |
| | | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 2 | μΑ |
| | | V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -2 | μΑ |
| R _{DSon} drain-source on-state resistance | drain-source on-state | V _{GS} = 10 V; I _D = 3 A; T _j = 25 °C | - | 54 | 72 | mΩ |
| | resistance | V _{GS} = 10 V; I _D = 3 A; T _j = 150 °C | - | 88 | 118 | mΩ |
| | V _{GS} = 4.5 V; I _D = 2.6 A; T _j = 25 °C | - | 70 | 100 | mΩ | |
| 9 _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 3 A; T_{j} = 25 °C | - | 9 | - | S |
| R_G | gate resistance | f = 1 MHz | - | 11.5 | - | Ω |
| Dynamic cl | haracteristics | 1 | 1 | | | |
| Q _{G(tot)} | total gate charge | V _{DS} = 15 V; I _D = 3 A; V _{GS} = 10 V; | - | 3.6 | 5.5 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.4 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.7 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; | - | 160 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 33 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 26 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 15 V; I_D = 3 A; V_{GS} = 10 V; | - | 6 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 6 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 11 | - | ns |
| t _f | fall time | | - | 4 | - | ns |
| Source-dra | in diode | 1 | | | 1 | |
| V _{SD} | source-drain voltage | I _S = 1 A; V _{GS} = 0 V; T _j = 25 °C | - | 0.8 | 1.2 | V |

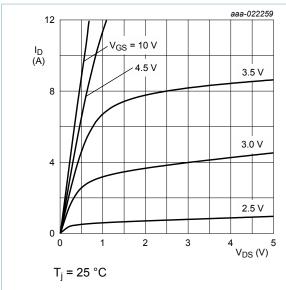


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

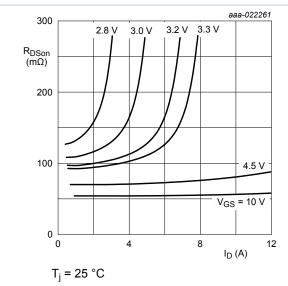


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

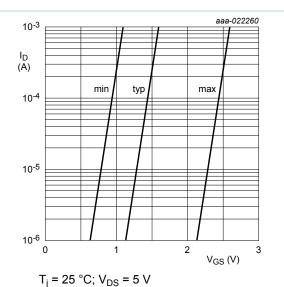


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

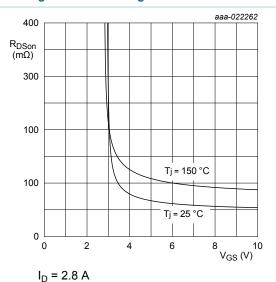


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

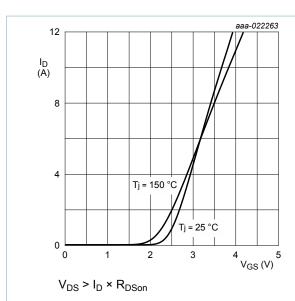


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

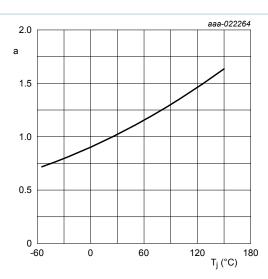


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

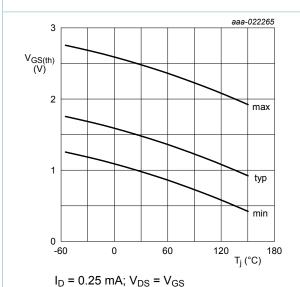
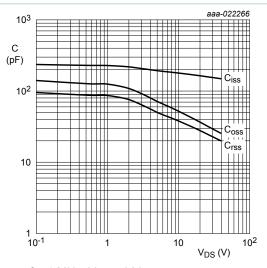


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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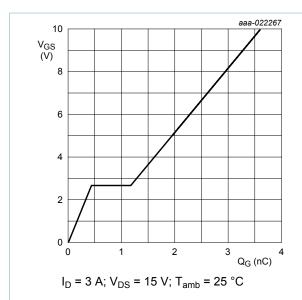


Fig. 14. Gate-source voltage as a function of gate charge; typical values

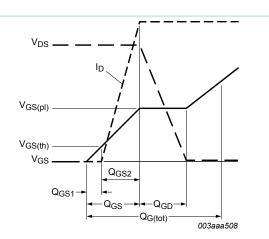


Fig. 15. MOSFET transistor: Gate charge waveform definitions

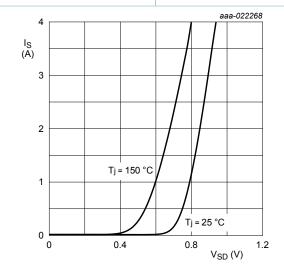
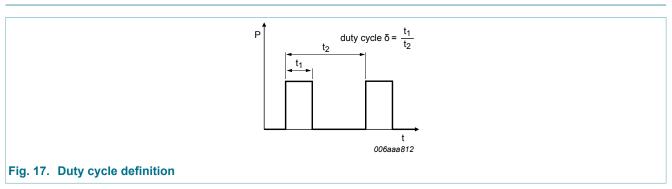


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



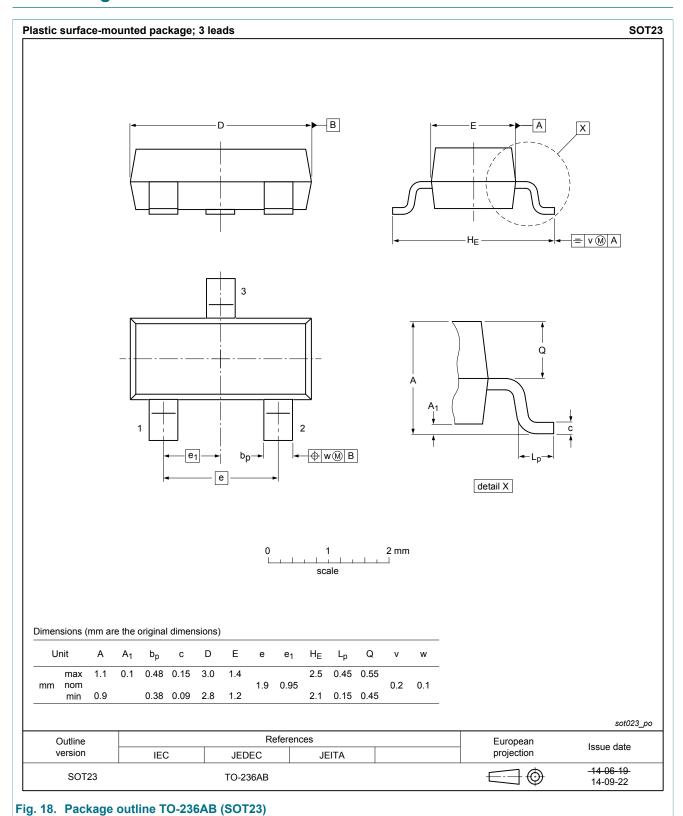
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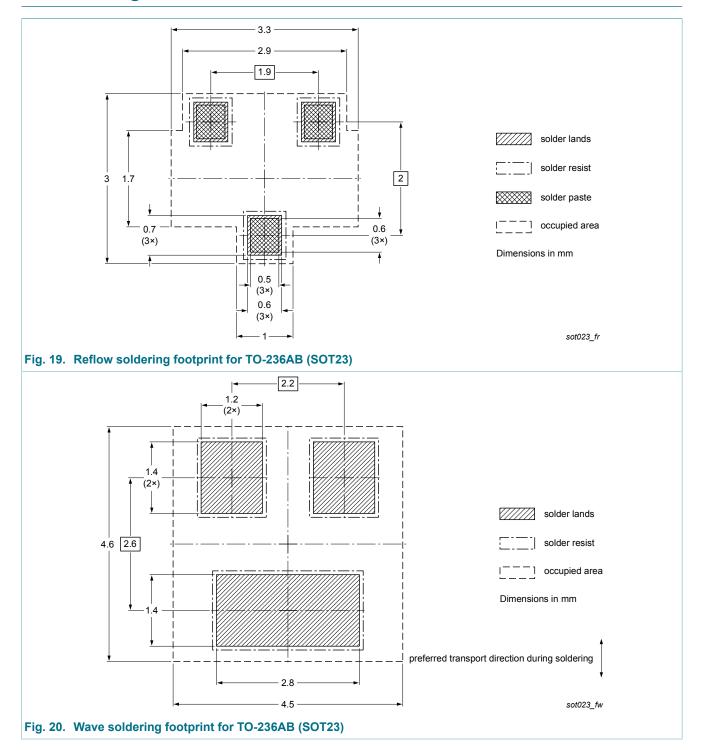
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMV90ENE v.1 | 20160420 | Product data sheet | - | - |

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
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